Radiation Tolerance and Mechanical Properties of Nanostructured Ceramic/Metal Composites

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Work supported by DOE, NE, Nuclear Energy Enabling Technologies

Presented at: Materials-Cross-Cut NEET Webinar August 20th, 2013



What is the problem Structural materials are prone to radiation damage: void swelling and embrittlement



D.L. Porter and F. A. Garner, J. Nuclear Materials, 159, p. 114 (1988)
D.J. Bacon and Y.N. Osetsky, Int. Mater. Rev., 47, p. 233 (2002).
H. Trinkaus and B.N. Singh, J. Nuclear Materials, 323, p. 229 (2003).

How to design radiation damage tolerant materials?



Defects that do NOT

Fracture of radiated 316 SS at RT

Approach to finding the solution in crystalline materials



coherency stresses

No coherency stresses

Grain and interphase boundaries are known to be defect sinks

B.N. Singh, J. Nucl. Mater., 46 (1973) 99; Phil. Mag. 28 (1973) 1409.B.N. Singh, S.J. Zinkle, J. Nucl. Mater., (1993).



M.J. Demkowicz, R.G. Hoagland, J.P. Hirth, *Physical Review Letters*, **100**, 136102 (2008).

W.Z. Han, A. Misra, M.J. Demkowicz, *et al. Acta Mater*. (2012).

Questions:

- Are the interfaces between crystalline and amorphous materials also effective defect sinks?
- How do amorphous materials respond to radiation damage

Mechanism #1: PKA creates isolated thermal spikes (liquids) that super quench to low-density zones (SQZs)



Mechanism #1 account for saturable swelling and ductilization in irradiated glasses

Mechanism #2: Thermal spike melting triggers polarized plastic deformation in unmelted material next to liquid zones



PRL in review (2013)

Approach

- Use high crystallization temperature Si-C-O amorphous alloys
 - $T_{cry} > 1000 \text{ C}$
 - Synthesize with PVD (100 300 nm)
 - Study thermal and irradiation stability
 - Model with MD
 - Evaluate mechanical properties
 - Make Zr doped Si-C-O to study with XAFS
- Develop Fe/ Si-C-O composites
 - Synthesize with PVD
 - Study thermal and irradiation stability
 - Model with MD
 - Evaluate mechanical properties

Schedule

Year 1: Synthesis of amorphous alloys, irradiation, and characterization of amorphous phase stability. Correlation of irradiation behavior to crystallization temperature. Development of empirical potentials and atomic structure descriptions for the amorphous alloys.

Year 2: Detailed experimental studies of irradiated amorphous alloys accompanied by modeling of cascade damage, defect behavior, swelling behavior, and diffusion. Synthesis of amorphous-ceramic/metal composites, begin irradiation studies. Year 3: Detailed experimental studies of irradiated composites accompanied by modeling of cascade damage, defect behavior, swelling behavior, and diffusion. Construction and experimental verification of theories linking atomic scale mechanisms to amorphous alloys and amorphous-ceramic/metal composite behavior under irradiation.

Composition Analysis Using X-ray Photoemission Spectroscopy (XPS)



(a) C 1s , (b) Si 2p and (c) O 1s core levels photoemission spectra for the amorphous alloy film. Photoelectrons were collected normal to the surface and the x-ray beam was incident at about 45°.

Composition Analysis Using X-ray Photoemission Spectroscopy (XPS)



Atomic composition from Si-C-O amorphous alloy film. The Si 2p, C 1s and O 1s core levels photoelectron intensities were used and the intensity ratios were corrected with the transmission function of the kinetic energy electron analyzer.

Average composition of the alloys from the XPS process.

Sputtering Ratio	Ideal Composition	Composition (No Annealing)	Composition (Vacuum Annealing)
1:1	Si _{1.00} C _{0.50} O _{1.00}	$Si_{1.00}C_{0.50}O_{1.13}$	Si _{1.00} C _{0.51} O _{1.27}
1:2	Si _{1.00} C _{0.33} O _{1.33}	$Si_{1.00}C_{0.22}O_{1.52}$	Si _{1.00} C _{0.37} O _{1.50}
2:1	Si _{1.00} C _{0.67} O _{0.67}	Si _{1.00} C _{0.75} O _{0.73}	Si _{1.00} C _{0.72} O _{0.82}

The sputtering ratio of the target materials are denoted as x:y, were x correspond to the rate of the SiC target and y to the rate of the SiO_2 target.

Effect of Annealing on XPS Peak Shape



The Si 2p core level spectra obtained for the 1:1 SiCO alloy (a) before and (b) after sputter depth profiling. Similar behaviors were observed with the 1:2 and 2:1 SiCO alloys.

X-ray Diffraction







Plans for upcoming modeling work

DFT calculation for lateral deformation

-11 Energy (eV/SiC) Revise ReaxFF by refitting SiC lateral deformation energy change. -12 -1360 100 80 volume (Å³)

 $SiO_{16}C_{02}$

- Development of MEAM potential for Si-C-O is underway at MSU.
- We will be using LAMMPS to carry out molecular dynamics simulations and Quantum ESPRESSO for DFT calculations.
- Large scale first principle MD will be carried out using QBox, which is designed for massive parallel computers (i.e. Mira at ANL).
- Two proposals have been submitted for supercomputing resources:
 - INCITE proposal (June) for 132 million core-hours at Mira, where we plan to carry out 5 keV PKA irradiation simulations in a 350x350x350 (~ 2 million atoms) cell as well as first principles MD with 500 atoms Compare MD results against exp.
 - XSEDE proposal (July) for 7 million core-hours.

For now:

- DFT calculations on defect and vacancy energies of C in SiO₂ structure for future comparison against MD potentials.
- Irradiation simulation in amorphous SiO₂ using ReaxFF to investigate thermal spikes.

Properties	SiOC	SiO_2
Density (g/cm ³)	2.35	2.20
Thermal expansion coefficient (10 ⁻⁶ /K)	3.14	0.5
Vickers Hardness (GPa)	7.0-8.6	6.0-7.0
Elastic Modulus (GPa)	97.9	70
Glass transition temperature (degee C)	1350	1190
Refractive index	1.58	1.46
Dielectric constant	4.4	4
Electric conductivity (/ Ω .cm)	4×10 ⁻¹³	~10 ⁻²²

J. Mater. Res. 6 (1991), 2723